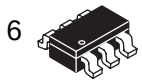
WEITRON

WIMN10

Surface Mount Switching Multi-Chip Diode Array

Lead(Pb)-Free

MULTI-CHIP DIODES
100m AMPERES
80 VOLTS



TSOP-6

Features:

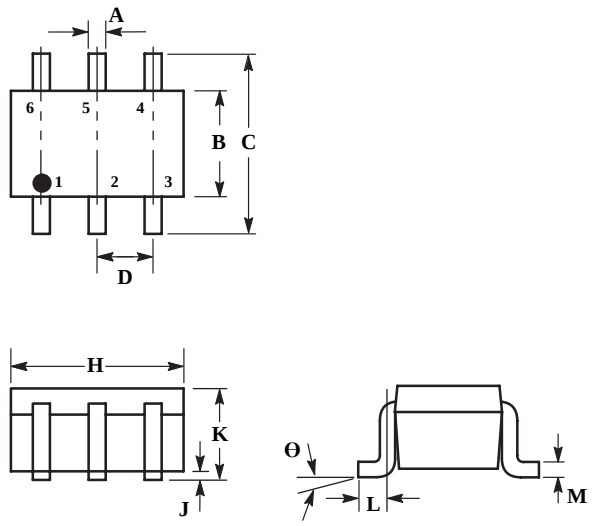
* Ultra High Speed Switching
* Ultra-Small Surface Mount Package
* For General Purpose Switching Applications
* High Conductance Power Dissipation

Mechanical Data:

* Case : TSOP-6
* Case Material : Molded Plastic. UL Flammability Classification Ration 94V-0
* Moisture Sensitivity : Level 1 per J-STD-020C
* Terminals : Solderable per MIL-STD-202, Method 208
* Polarity : See Diagram

TSOP-6 Outline Dimensions

Unit:mm



TSOP-6		
Dim	**Min**	**Max**
A	0.25	0.50
B	1.30	1.70
C	2.50	3.00
D	0.85	1.05
Θ	0°	10°
H	2.90	3.10
J	0.01	0.10
K	0.90	1.10
L	0.20	0.60
M	0.10	0.26

Maximum Ratings @ T_A= 25°C unless otherwise specified

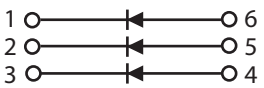
Characteristic	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	80	V
DC Reverse Voltage	V_R	80	V
Peak Forward Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	100	mA
Non-Repetitive Peak Forward Surge Current @ t = 1.0s	I_{FSM}	4.0	A
Power Dissipation (Note 1)	P_D	300	mW
Operating Temperature Range	T_j	+150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

Note 1 : Not to exceed 200mW per element.

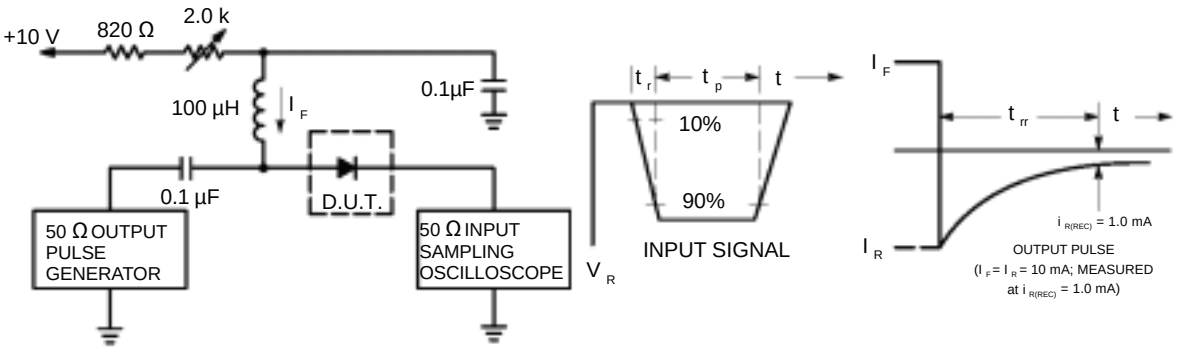
Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit
Forward Voltage I_F = 100mA	V_F	-	1.2	V
Reverse Current V_R = 70V	I_R	-	0.1	μA
Capacitance between terminals V_R = 6V, f = 1.0MHz	C_T	-	3.5	pF
Reverse Recovery Time V_R = 6V, I_F =5mA	T_{rr}	-	4.0	ns

Device Marking

Item	Marking	Eqivalent Circuit diagram
WIMN10	N10	

Typical Characteristics



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

CURVES APPLICABLE TO EACH DIODE

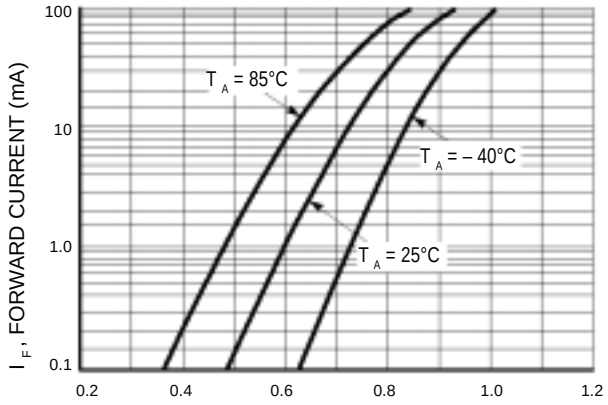


Figure 2. Forward Voltage

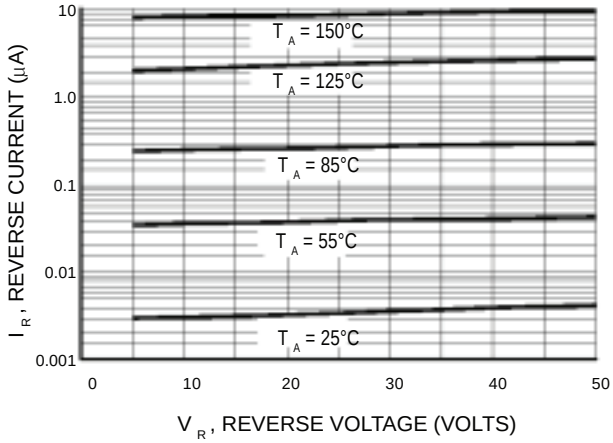


Figure 3. Leakage Current

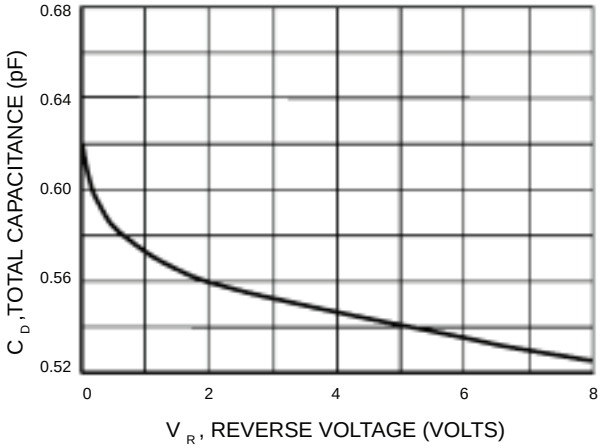


Figure 4. Capacitance